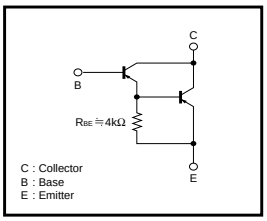
Power transistor (–40V, –2A)

2SB1183 / 2SB1239

●Features

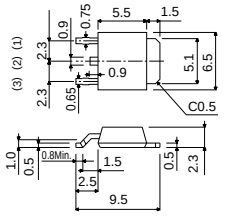
1) Darlington connection for high DC current gain.
2) Built-in 4kΩ resistor between base and emitter.
3) Complements the 2SD1759 / 2SD1861.

●Equivalent circuit



●External dimensions (Units : mm)

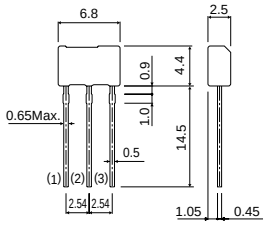
2SB1183



ROHM : CPT3
EIAJ : SC-63

(1) Base(Gate)
(2) Collector(Drain)
(3) Emitter(Source)

2SB1239



Taping specifications

ROHM : ATV

(1) Emitter
(2) Collector
(3) Base

●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Collector-base voltage		V_{CBO}	–40	V
Collector-emitter voltage		V_{CER}	–40	V
Emitter-base voltage		V_{EBO}	–5	V
Collector current		I_C	–2	A(DC)
			–3	A(Pulse) *1
Collector power dissipation	2SB1183	P_C	1	W
			10	W(Tc=25°C)
	2SB1239		1	W *2
Junction temperature		Tj	150	°C
Storage temperature		Tstg	–55~+150	°C

*1 Single pulse Pw=10ms
*2 Printed circuit board 1.7 mm thick, collector plating 100mm² or larger.

●Packaging specifications and h_{FE}

Type	2SB1183	2SB1239
Package	CPT3	ATV
h_{FE}	1k~200k	1k~
Code	TL	T146
Basic ordering unit (pieces)	2500	2500

●Electrical characteristics (Ta=25°C)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage		BV_{CBO}	–40	–	–	V	I_C=–50μA
Collector-emitter breakdown voltage		BV_{CER}	–40	–	–	V	I_C=–1mA, R_{BE}=10kΩ
Emitter-base breakdown voltage		BV_{EBO}	–5	–	–	V	I_E=–50μA
Collector cutoff current		I_{CBO}	–	–	–1	μA	V_{CB}=–24V
Emitter cutoff current		I_{EBO}	–	–	–1	μA	V_{EB}=–4V
Collector-emitter saturation voltage		$V_{CE(sat)}$	–	–	–1.5	V	I_C/I_B=–0.6A/–1.2mA
DC current transfer ratio	2SB1183	h_{FE}	1000	–	20000	–	V_{CE}/I_C=–2V/–0.5A
	2SB1239		1000	–	–	–	
Output capacitance		Cob	–	11	–	pF	V_{CB}=–10V, I_E=0A, f=1MHz

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ROHM Semiconductor:

2SB1183TL